

32Kx8 bit Low Power CMOS Static RAM

FEATURES

- Process Technology : 0.7μm CMOS
- Organization : 32Kx8
- Power Supply Voltage : Single 5V ±10%
- Low Data Retention Voltage : 2V(Min)
- Three state output and TTL Compatible
- Package Type : JEDEC Standard
- 28-DIP, 28-SOP, 28-TSOP I -Forward/Reverse

GENERAL DESCRIPTION

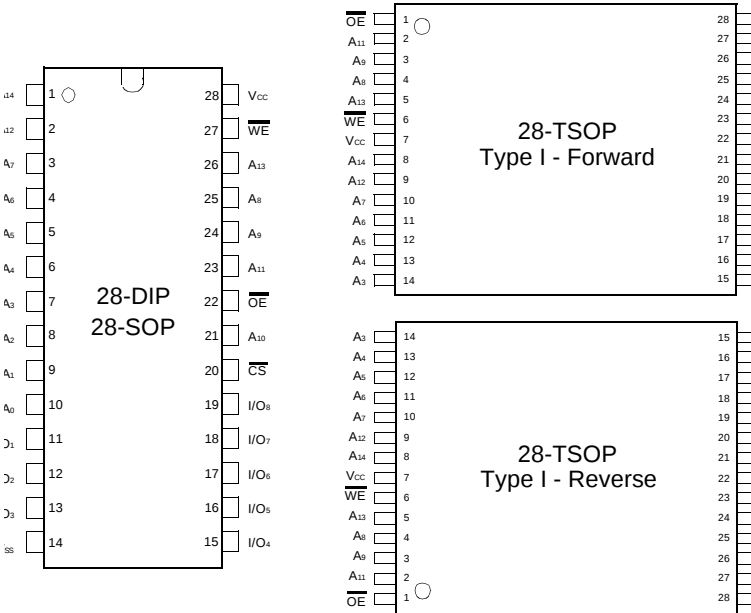
The KM62256C family is fabricated by SAMSUNG's advanced CMOS process technology. The family can support various operating temperature ranges and has various package types for user flexibility of system design. The family also support low data retention voltage for battery back-up operation with low data retention current.

PRODUCT FAMILY

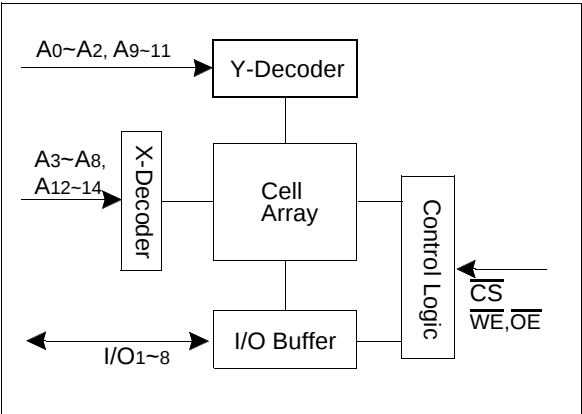
Product Family	Operating Temperature.	Speed (ns)	PKG Type	Power Dissipation	
				Standby (I _{SB1} , Max)	Operating (I _{CC2})
KM62256CL KM62256CL-L	Commercial (0~70°C)	45*/55/70ns	28-DIP, 28-SOP 28-TSOP I R/F	100μW 20μW	70mA
KM62256CLE KM62256CLE-L	Extended (-25~85°C)	70/100ns	28-SOP 28-TSOP I R/F	100μW 50μW	
KM62256CLI KM62256CLI-L	Industrial (-40~85°C)	70/100ns	28-SOP 28-TSOP I R/F	100μW 50μW	

* The parameter is measured with 30pF test load.

PIN DESCRIPTION



FUNCTIONAL BLOCK DIAGRAM



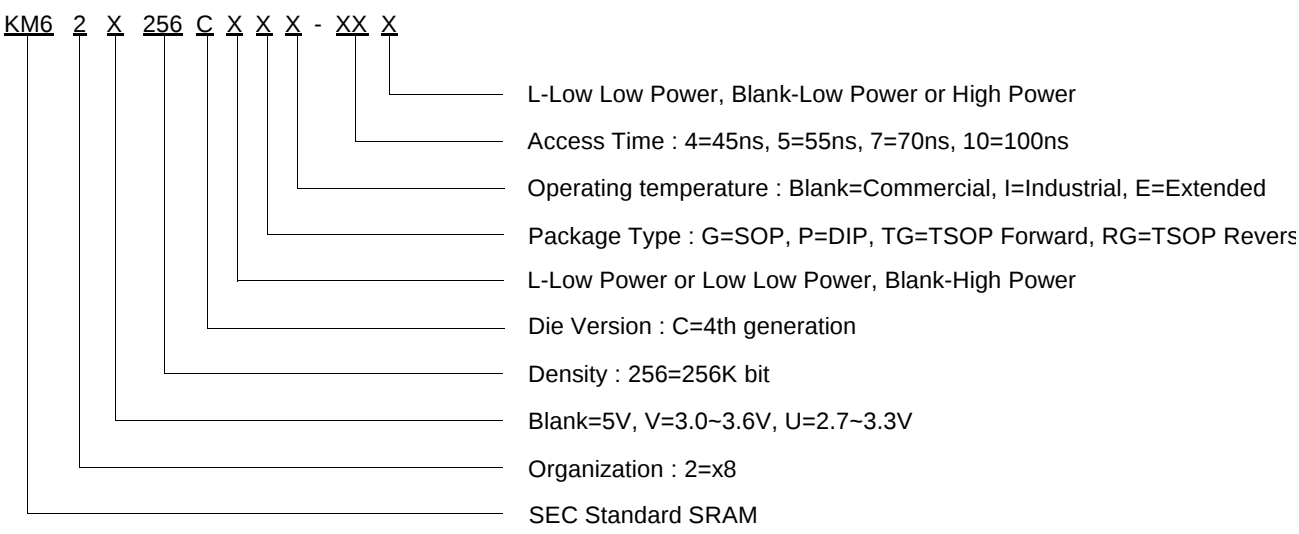
Name	Function
A ₀ ~A ₁₄	Address Inputs
WE	Write Enable Input
CS	Chip Select Input
OE	Output Enable Input
I/O ₁ ~I/O ₈	Data Inputs/Outputs
V _{CC}	Power(5V)
V _{SS}	Ground

PRODUCT LIST & ORDERING INFORMATION

PRODUCT LIST

Commercial Temp Product (0~70jE)		Extended Temp Products (-25~85jE)		Industrial Temp Products (-40~85jE)	
Part Name	Function	Part Name	Function	Part Name	Function
KM62256CLP-4	28-DIP, 45ns, L-pwr	KM62256CLGE-7	28-SOP, 70ns, L-pwr	KM62256CLGI-7	28-SOP, 70ns, L-pwr
KM62256CLP-4L	28-DIP, 45ns, LL-pwr	KM62256CLGE-7L	28-SOP, 70ns, LL-pwr	KM62256CLGI-7L	28-SOP, 70ns, LL-pwr
KM62256CLP-5	28-DIP, 55ns, L-pwr	KM62256CLGE-10	28-SOP, 100ns, L-pwr	KM62256CLGI-10	28-SOP, 100ns, L-pwr
KM62256CLP-5L	28-DIP, 55ns, LL-pwr	KM62256CLGE-10L	28-SOP, 100ns, LL-pwr	KM62256CLGI-10L	28-SOP, 100ns, LL-pwr
KM62256CLP-7	28-DIP, 70ns, L-pwr	KM62256CLTGE-7	28-TSOP F, 70ns, L-pwr	KM62256CLTGI-7	28-TSOP F, 70ns, L-pwr
KM62256CLP-7L	28-DIP, 70ns, LL-pwr	KM62256CLTGE-7L	28-TSOP F, 70ns, LL-pwr	KM62256CLTGI-7L	28-TSOP F, 70ns, LL-pwr
KM62256CLG-4	28-SOP, 45ns, L-pwr	KM62256CLTGE-10	28-TSOP F, 100ns, L-pwr	KM62256CLTGI-10	28-TSOP F, 100ns, L-pwr
KM62256CLG-4L	28-SOP, 45ns, LL-pwr	KM62256CLTGE-10L	28-TSOP F, 100ns, LL-pwr	KM62256CLTGI-10L	28-TSOP F, 100ns, LL-pwr
KM62256CLG-5	28-SOP, 50ns, L-pwr	KM62256CLRGE-7	28-TSOP R, 70ns, L-pwr	KM62256CLRGI-7	28-TSOP R, 70ns, L-pwr
KM62256CLG-5L	28-SOP, 50ns, LL-pwr	KM62256CLRGE-7L	28-TSOP R, 70ns, LL-pwr	KM62256CLRGI-7L	28-TSOP R, 70ns, LL-pwr
KM62256CLG-7	28-SOP, 70ns, L-pwr	KM62256CLRGE-10	28-TSOP R, 100ns, L-pwr	KM62256CLRGI-10	28-TSOP R, 100ns, L-pwr
KM62256CLG-7L	28-SOP, 70ns, LL-pwr	KM62256CLRGE-10L	28-TSOP R, 100ns, LL-pwr	KM62256CLRGI-10L	28-TSOP R, 100ns, LL-pwr
KM62256CLTG-4	28-TSOP F, 45ns, L-pwr				
KM62256CLTG-4L	28-TSOP F, 45ns, LL-pwr				
KM62256CLTG-5	28-TSOP F, 55ns, L-pwr				
KM62256CLTG-5L	28-TSOP F, 55ns, LL-pwr				
KM62256CLTG-7	28-TSOP F, 70ns, L-pwr				
KM62256CLTG-7L	28-TSOP F, 70ns, LL-pwr				
KM62256CLRG-4	28-TSOP R, 45ns, L-pwr				
KM62256CLRG-4L	28-TSOP R, 45ns, LL-pwr				
KM62256CLRG-5	28-TSOP R, 55ns, L-pwr				
KM62256CLRG-5L	28-TSOP R, 55ns, LL-pwr				
KM62256CLRG-7	28-TSOP R, 70ns, L-pwr				
KM62256CLRG-7L	28-TSOP R, 70ns, LL-pwr				

ORDERING INFORMATION



ABSOLUTE MAXIMUM RATINGS*

Item	Symbol	Ratings	Unit	Remark
Voltage on any pin relative to Vss	VIN,VOUT	-0.5 to Vcc+0.5	V	-
Voltage on Vcc supply relative to Vss	Vcc	-0.5 to 7.0	V	-
Power Dissipation	Pd	1.0	W	-
Storage temperature	TSTG	-65 to 150	°C	-
Operating Temperature	TA	0 to 70	°C	KM62256CL/L-L
		-25 to 85	°C	KM62256CLE/LE-L
		-40 to 85	°C	KM62256CLI/LI-L
Soldering temperature and time	TSOLDER	260°C, 10sec (Lead Only)	-	-

* Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operating section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

RECOMMENDED DC OPERATING CONDITIONS*

Item	Symbol	Min	Typ**	Max	Unit
Supply voltage	Vcc	4.5	5.0	5.5	V
Ground	Vss	0	0	0	V
Input high voltage	VIH	2.2	-	Vcc+0.5V	V
Input low voltage	VIL	-0.5***	-	0.8	V

* 1) Commercial Product : TA=0 to 70°C, unless otherwise specified
2) Extended Product : TA=-25 to 85°C, unless otherwise specified
3) Industrial Product : TA=-40 to 85°C, unless otherwise specified
** TA=25°C
*** VIL(min)=-3.0V for tP 50ns pulse width

CAPACITANCE* (f=1MHz, TA=25°C)

Item	Symbol	Test Condition	Min	Max	Unit
Input capacitance	CIN	VIN=0V	-	6	pF
Input/Output capacitance	CIO	VIO=0V	-	8	pF

* Capacitance is sampled not 100% tested

KM62256C Family

CMOS SRAM

DC AND OPERATING CHARACTERISTICS

Item		Symbol	Test Conditions*	Min	Typ**	Max	Unit
Input leakage current		I _{LI}	V _{IN} =V _{SS} to V _{CC}	-1	-	1	§Ě
Output leakage current		I _{LO}	$\overline{CS}=V_{IH}$ or $\overline{WE}=V_{IL}$ V _{IO} =V _{SS} to V _{CC}	-1	-	1	§Ě
Operating power supply current		I _{CC}	$\overline{CS}=V_{IL}$, V _{IN} =V _{IH} or V _{IL} , I _{IO} =0mA	-	7	15***	mA
Average operating current		I _{CC1}	Cycle time=1§Ě 100% duty $\overline{CS}_i \hat{A} 0.2V$, V _{IL} Ě 0.2V V _{IN} Ě V _{CC} -0.2V, I _{IO} =0mA	-	-	7****	mA
		I _{CC2}	Min cycle, 100% duty $\overline{CS}=V_{IL}$, I _{IO} =0mA	-	-	70	mA
Output low voltage		V _{OL}	I _{OL} =2.1mA	-	-	0.4	V
Output high voltage		V _{OH}	I _{OH} =-1.0mA	2.4	-	-	V
Standby Current(TTL)		I _{SB}	$\overline{CS}=V_{IH}$	-	-	1*****	mA
Standby Current (CMOS)	KM62256CL KM62256CL-L	I _{SB1}	$\overline{CS}_i \hat{A} V_{CC}-0.2V$ V _{IN} Ě 0.2V or V _{IN} Ě V _{CC} -0.2V	L(Low Power)	-	2	§Ě
				LL(L Low Power)	-	1	§Ě
	KM62256CLE KM62256CLE-L			L(Low Power)	-	-	§Ě
				LL(L Low Power)	-	-	§Ě
	KM62256CLI KM62256CLI-L			L(Low Power)	-	-	§Ě
				LL(L Low Power)	-	-	§Ě

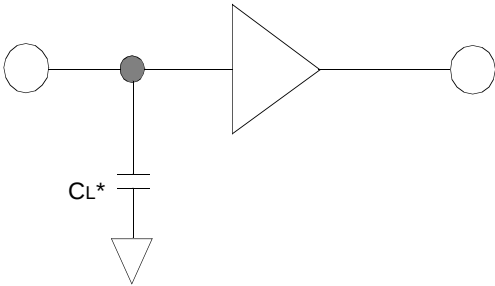
* 1) Commercial Product : T_A=0 to 70 Ě, V_{CC}=5V Ě 10% unless otherwise specified
 2) Extended Product : T_A=-25 to 85 Ě, V_{CC}=5V Ě 10% nless otherwise specified
 3) Industrial Product : T_A=-40 to 85 Ě, V_{CC}=5V Ě 10% unless otherwise specified
 ** T_A=25 Ě
 *** 20mA for Extended and Industrial Products
 ****10mA for Extended and Industrial Products
 *****2mA for Extended and Industrial Products

A.C CHARACTERISTICS

TEST CONDITIONS(1.Test Load and Test Input/Output Reference)*

Item	Value	Remark
Input pulse level	0.8 to 2.4V	-
Input rising & falling time	5ns	-
input and output reference voltage	1.5V	-
Output load (See right)	C _L =100pF+1TTL	-
	**C _L =30pF+1TTL	-

* See DC Operating conditions
 ** Test load for 45ns commercial products



* Including scope and jig capacitance

KM62256C Family

CMOS SRAM

TEST CONDITIONS(2. Temperature and Vcc Conditions)

Product Family	Temperature	Power Supply(Vcc)	Speed Bin	Comments
KM62256CL/L-L	0~70℃	5V ±10%	45*/55/70ns	Commercial
KM62256CLE/LE-L	-25~85℃	5V ±10%	70/100ns	Extended
KM62256CLI/LI-L	-40~85℃	5V ±10%	70/100ns	Industrial

* The parameter is measured with 30pF test load

PARAMETER LIST FOR EACH SPEED BIN

Parameter List		Symbol	Speed Bins								Units
			45ns*		55ns		70ns		100ns		
			Min	Max	Min	Max	Min	Max	Min	Max	
Read	Read cycle time	tRC	45	-	55	-	70	-	100	-	ns
	Address access time	tAA	-	45	-	55	-	70	-	100	ns
	Chip select to output	tCO	-	45	-	55	-	70	-	100	ns
	Output enable to valid output	tOE	-	25	-	25	-	35	-	50	ns
	Chip select to low-Z output	tLZ	10	-	10	-	10	-	10	-	ns
	Output enable to low-Z output	tOLZ	5	-	5	-	5	-	5	-	ns
	Chip disable to high-Z output	tHZ	0	20	0	20	0	30	0	35	ns
	Output disable to high-Z output	tOHZ	0	20	0	20	0	30	0	35	ns
	Output hold from address change	tOH	5	-	5	-	5	-	5	-	ns
Write	Write cycle time	tWC	45	-	55	-	70	-	100	-	ns
	Chip select to end of write	tCW	45	-	45	-	60	-	80	-	ns
	Address set-up time	tAS	0	-	0	-	0	-	0	-	ns
	Address valid to end of write	tAW	45	-	45	-	60	-	80	-	ns
	Write pulse width	tWP	40	-	40	-	50	-	60	-	ns
	Write recovery time	tWR	0	-	0	-	0	-	0	-	ns
	Write to output high-Z	tWHZ	0	20	0	20	0	25	0	35	ns
	Data to write time overlap	tDW	25	-	25	-	30	-	50	-	ns
	Data hold from write time	tDH	0	-	0	-	0	-	0	-	ns
	End write to output low-Z	tOW	5	-	5	-	5	-	5	-	ns

* The parameter is measured with 30pF test load

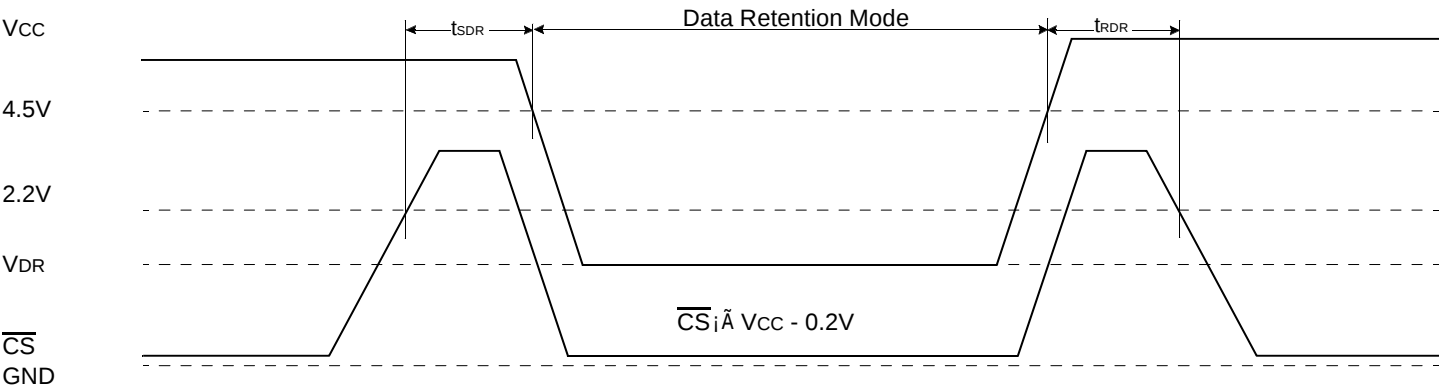
DATA RETENTION CHARACTERISTICS

Item	Symbol		Test Condition*		Min	Typ**	Max	Unit
Vcc for data retention	VDR		$\overline{CS}_i \nrightarrow V_{cc}-0.2V$		2.0	-	5.5	V
Data retention current	IDR	KM62256CL KM62256CL-L	$V_{cc}=3.0V$ $\overline{CS}_i \nrightarrow V_{cc}-0.2V$	L-Ver LL-Ver	- -	1 0.5	50 10	μA
		KM62256CLE KM62256CLE-L		L-Ver LL-Ver	- -	- -	50 25	
		KM62256CLI KM62256CLI-L		L-Ver LL-Ver	- -	- -	50 25	
Data retention set-up time	tSDR		See data retention waveform		0	-	-	ms
Recovery time	tRDR				5	-	-	

* 1) Commercial Product : Ta=0 to 70℃, unless otherwise specified
2) Extended Product : Ta=-25 to 85℃, unless otherwise specified
3) Industrial Product : Ta=-40 to 85℃, unless otherwise specified
** TA=25℃

DATA RETENTION WAVE FORM

1) $\overline{CS}$ Controlled



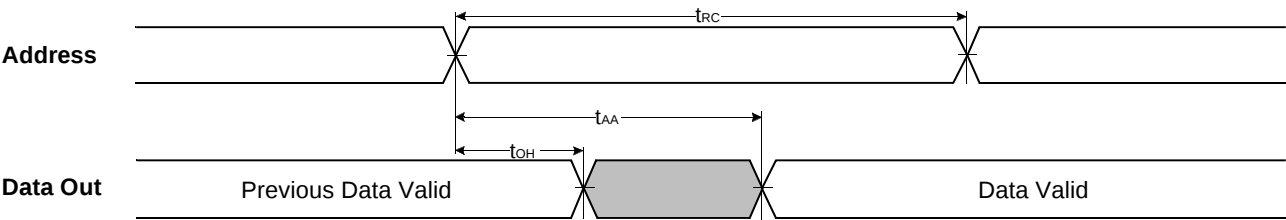
FUNCTIONAL DESCRIPTION

$\overline{CS}$	$\overline{WE}$	$\overline{OE}$	Mode	I/O Pin	Current Mode
H	X	X	Power Down	High-Z	ISB ISB1
L	H	H	Output Disable	High-Z	ICC
L	H	L	Read	Dout	ICC
L	L	X	Write	Din	ICC

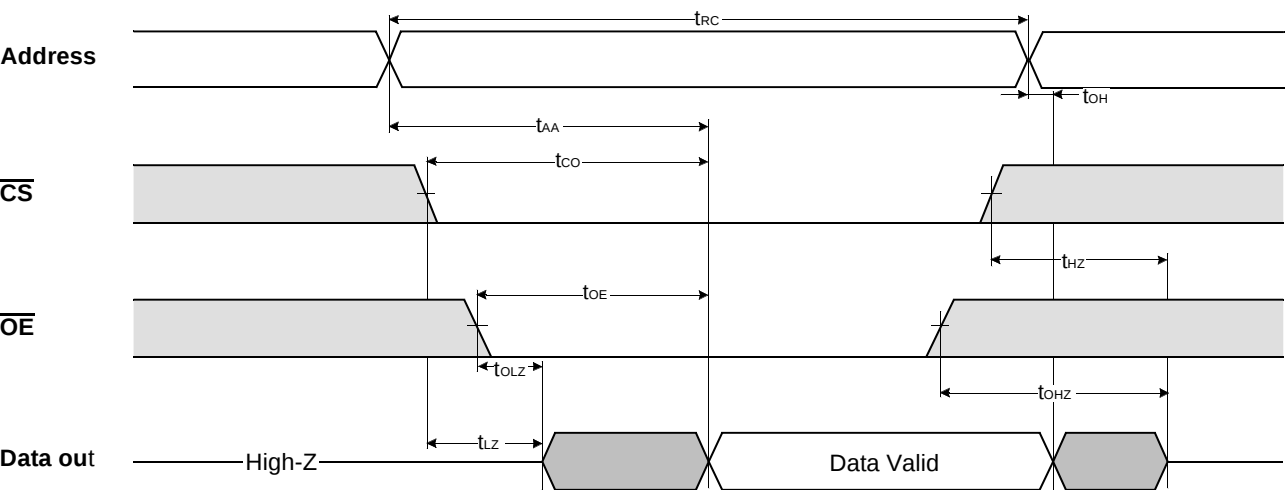
* X means don't care

TIMMING DIAGRAMS

TIMING WAVEFORM OF READ CYCLE (1) Address Controlled
($\overline{CS}=\overline{OE}=V_{IL}$, $\overline{WE}=V_{IH}$)



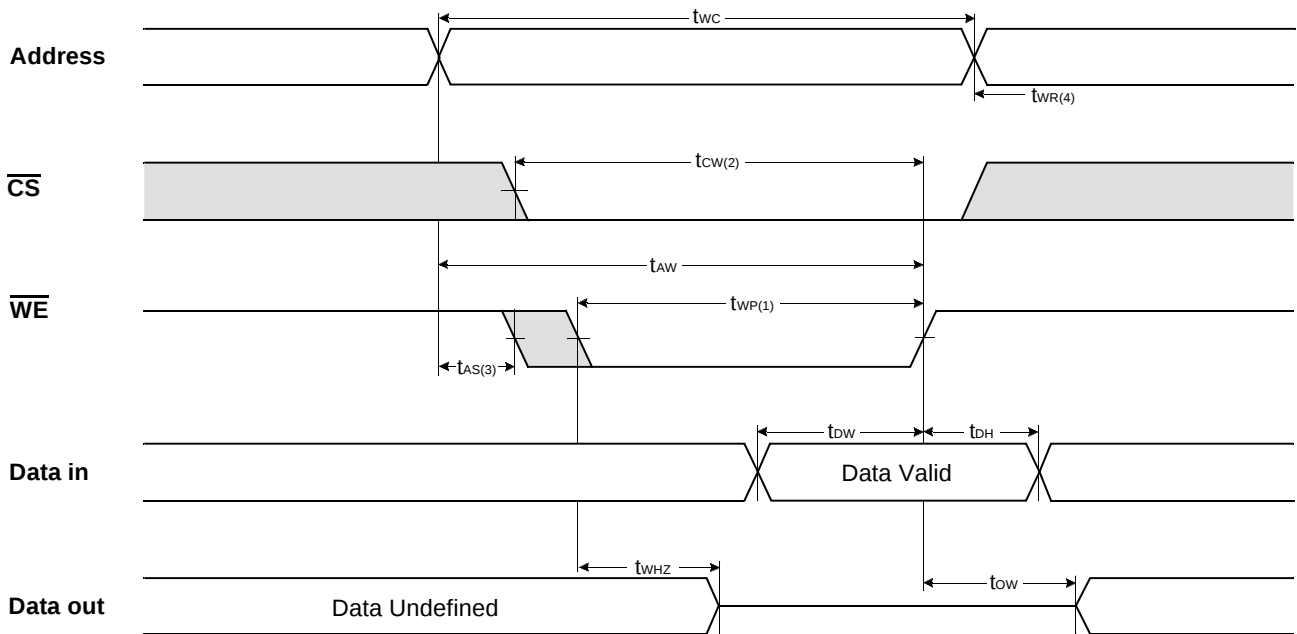
TIMING WAVEFORM OF READ CYCLE (2) $\overline{WE}=V_{IH}$



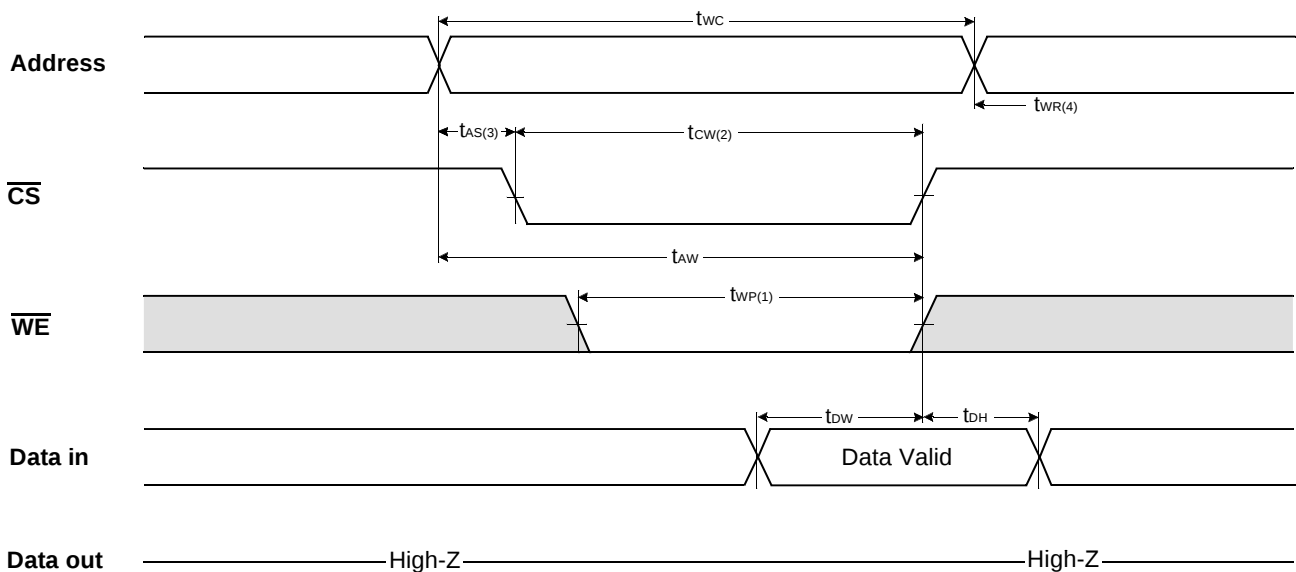
NOTES (READ CYCLE)

1. t_{HZ} and t_{OHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referenced to output voltage levels.
2. At any given temperature and voltage condition, $t_{HZ}(\text{max.})$ is less than $t_{LZ}(\text{min.})$ both for a given device and from device to device.

TIMING WAVEFORM OF WRITE CYCLE(1) $\overline{WE}$ Controlled



TIMING WAVEFORM OF WRITE CYCLE(2) $\overline{CS}$ Controlled



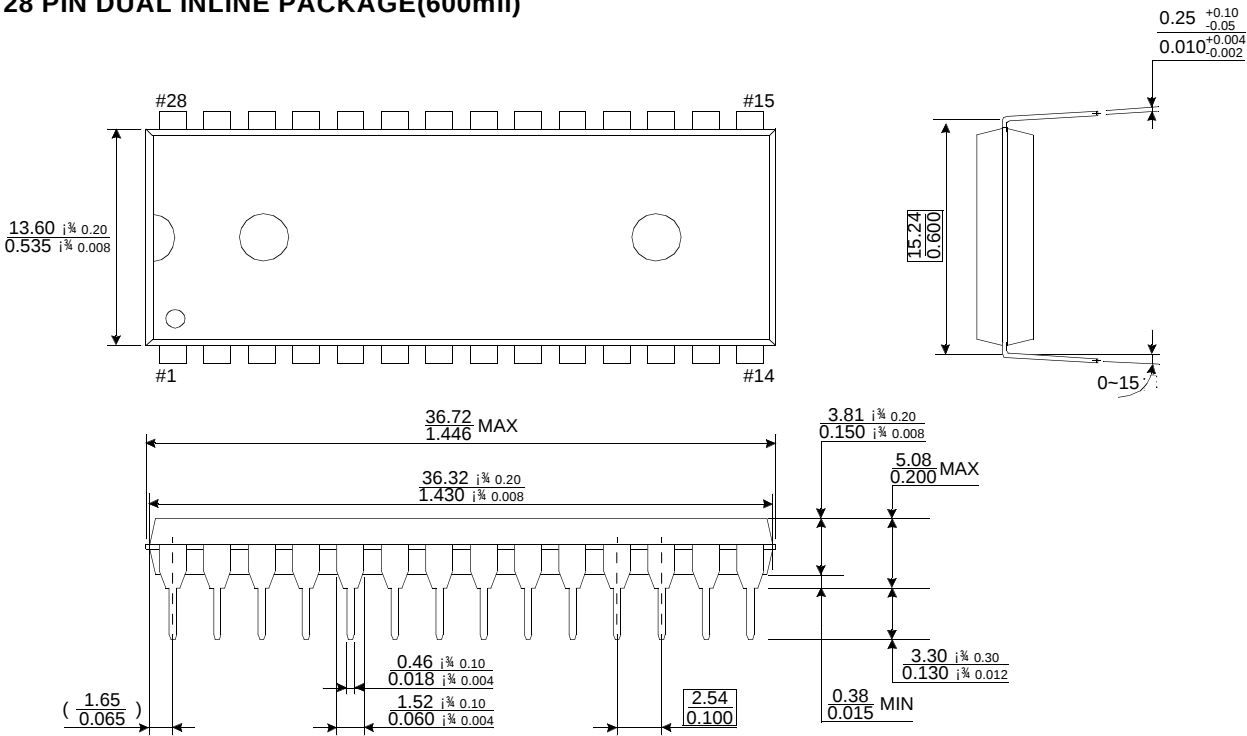
NOTES (WRITE CYCLE)

1. A write occurs during the overlap(t_{WP}) of low $\overline{CS}$ and low $\overline{WE}$. A write begins at the latest transition among $\overline{CS}$ goes low and $\overline{WE}$ going low : A write end at the earliest transition among $\overline{CS}$ going high and $\overline{WE}$ going high, t_{WP} is measured from the beginning of write to the end of write.
2. t_{CW} is measured from the $\overline{CS}$ going low to end of write.
3. t_{AS} is measured from the address valid to the beginning of write.
4. t_{WR} is measured from the end of write to the address change. t_{WR} applied in case a write ends as $\overline{CS}$ or $\overline{WE}$ going high.

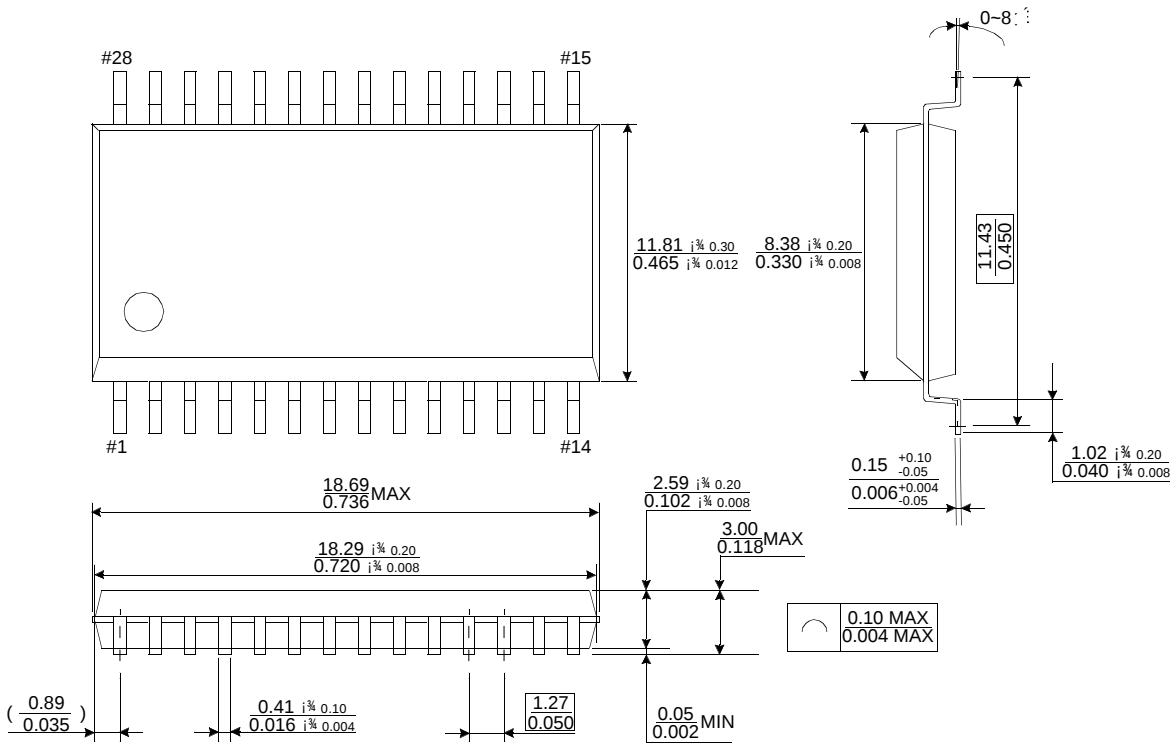
PACKAGE DIMENSIONS

Units :Millimeters(Inches)

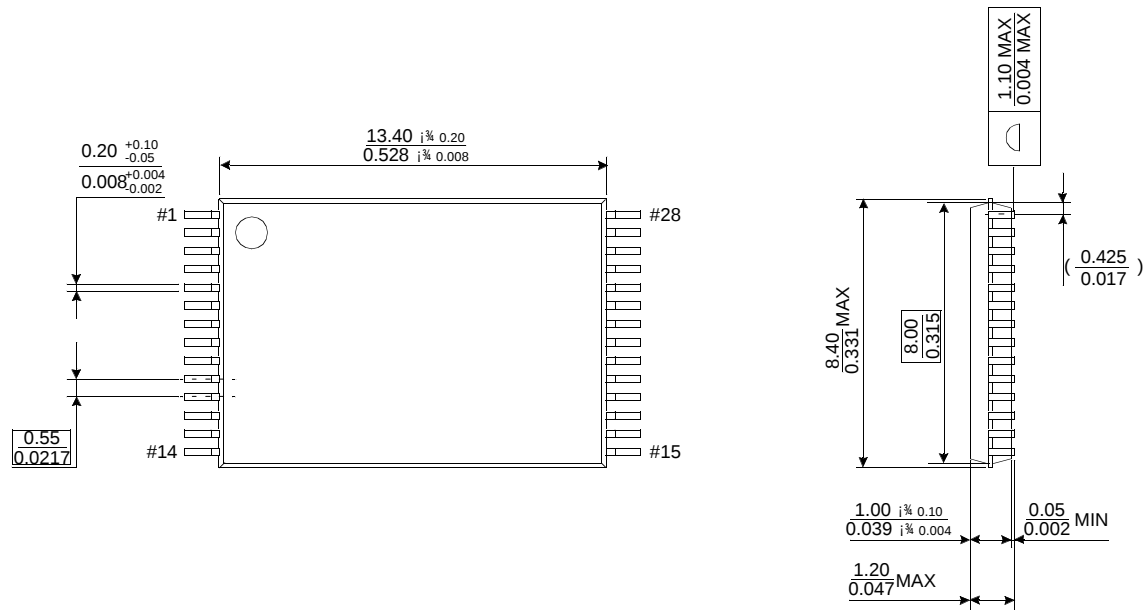
28 PIN DUAL INLINE PACKAGE(600mil)



28 PIN PLASTIC SMALL OUTLINE PACKAGE(450mil)



28 PIN THIN SMALL OUTLINE PACKAGE TYPE I (0813.4F)



28 PIN THIN SMALL OUTLINE PACKAGE TYPE I (0813.4R)

